

NTMFS4983NF

Power MOSFET

30 V, 106 A, Single N-Channel, SO-8 FL

Features

- Integrated Schottky Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- CPU Power Delivery
- Synchronous Rectification for DC-DC Converters
- Low Side Switching
- Telecom Secondary Side Rectification

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	30	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJA} (Note 1)	Steady State	T _A = 25°C	I _D	30	A
		T _A = 85°C		22	
Power Dissipation R _{θJA} (Note 1)		T _A = 25°C	P _D	3.13	W
Continuous Drain Current R _{θJA} ≤ 10 sec		T _A = 25°C	I _D	48	A
		T _A = 85°C		34	
Power Dissipation R _{θJA} , t ≤ 10 sec		T _A = 25°C	P _D	7.7	W
Continuous Drain Current R _{θJA} (Note 2)		T _A = 25°C	I _D	22	A
		T _A = 85°C		16	
Power Dissipation R _{θJA} (Note 2)		T _A = 25°C	P _D	1.7	W
Continuous Drain Current R _{θJC} (Note 1)		T _C = 25°C	I _D	106	A
		T _C = 85°C		76	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	38	W
Pulsed Drain Current	t _p =10μs	T _A = 25°C	I _{DM}	320	A
Current limited by package		T _A = 25°C	I _{Dmaxpkg}	100	A
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to +150	°C
Source Current (Body Diode)			I _S	54	A
Drain to Source dV/dt			dV/dt	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy (V _{DD} = 50 V, V _{GS} = 10 V, I _L = 45 A _{pk} , L = 0.1 mH, R _G = 25 Ω)			EAS	101	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

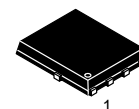
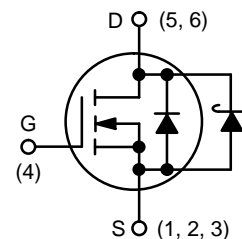


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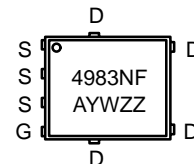
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	2.1 m Ω @ 10 V	106 A
	3.1 m Ω @ 4.5 V	

N-CHANNEL MOSFET



SO-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4983NFT1G	SO-8FL (Pb-Free)	1500 / Tape & Reel
NTMFS4983NFT3G	SO-8FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.3	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	40	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	74	
Junction-to-Ambient – $t \leq 10$ sec	$R_{\theta JA}$	16.3	

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 10\text{ mA}$, referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$ $T_J = 25^\circ\text{C}$			500	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 1.0\text{ mA}$	1.2	1.7	2.3	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 10\text{ mA}$, referenced to 25°C		5.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ $I_D = 30\text{ A}$		1.6	2.1	mΩ
		$I_D = 15\text{ A}$		1.6		
		$V_{GS} = 4.5\text{ V}$ $I_D = 30\text{ A}$		2.5	3.1	
		$I_D = 15\text{ A}$		2.5		
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		60		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		3250		pF
Output Capacitance	C_{OSS}			1340		
Reverse Transfer Capacitance	C_{RSS}			90		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		22.6		nC
Threshold Gate Charge	$Q_{G(TH)}$			2.9		
Gate-to-Source Charge	Q_{GS}			7.0		
Gate-to-Drain Charge	Q_{GD}			6.9		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		47.9		nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		13.5		ns
Rise Time	t_r			24.9		
Turn-Off Delay Time	$t_{d(OFF)}$			28.7		
Fall Time	t_f			10.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		9.4		ns
Rise Time	t_r			16.7		
Turn-Off Delay Time	$t_{d(OFF)}$			35.2		
Fall Time	t_f			7.4		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 2\text{ A}$	$T_J = 25^\circ\text{C}$		0.4	0.7	V
			$T_J = 125^\circ\text{C}$		0.32		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 2\text{ A}$			45		ns
Charge Time	t_a				23		
Discharge Time	t_b				22		
Reverse Recovery Charge	Q_{RR}				50		nC

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		0.65		nH
Drain Inductance	L_D			0.20		
Gate Inductance	L_G			1.5		
Gate Resistance	R_G			1.0		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

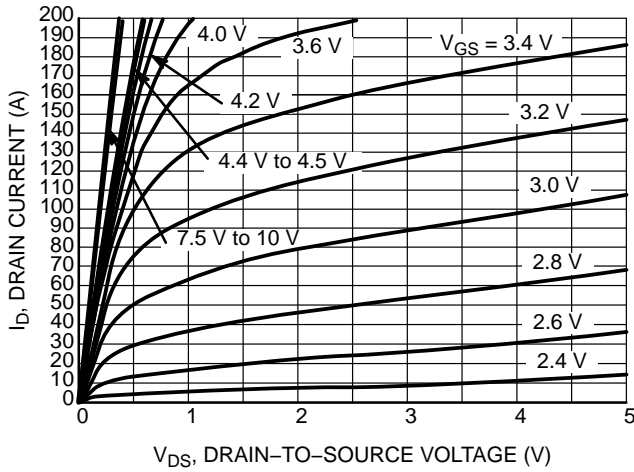


Figure 1. On-Region Characteristics

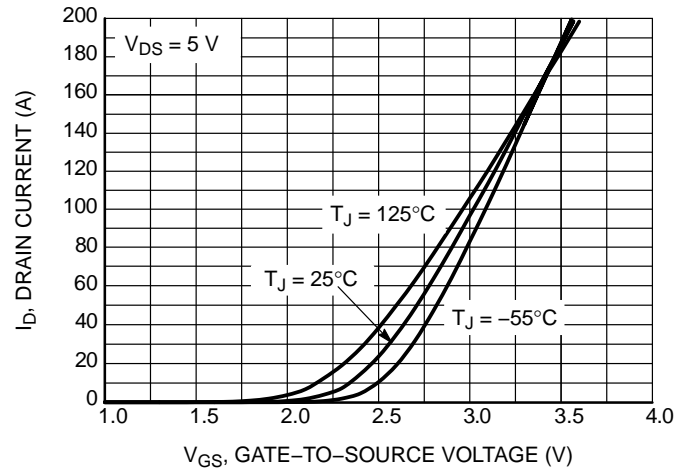


Figure 2. Transfer Characteristics

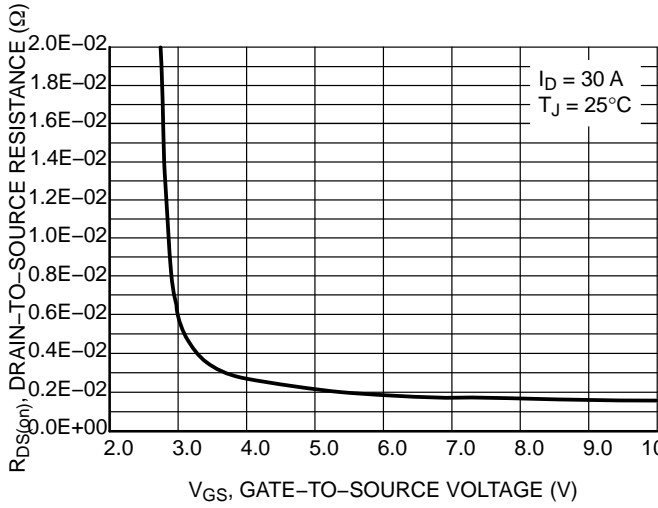


Figure 3. On-Resistance vs. Gate-to-Source Voltage

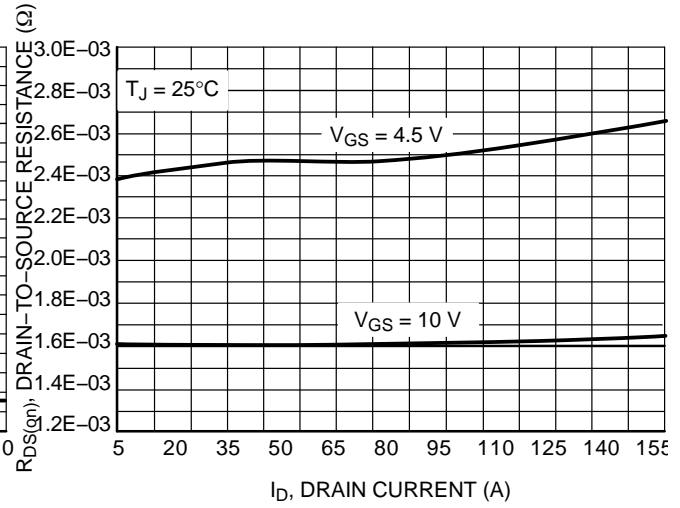


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

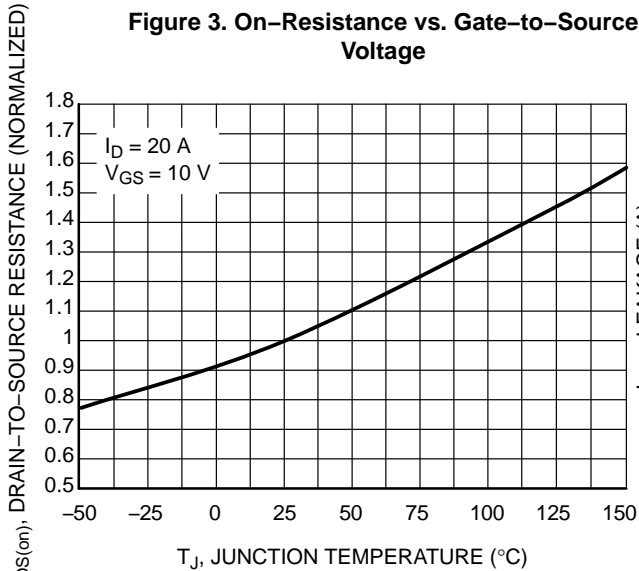


Figure 5. On-Resistance Variation with Temperature

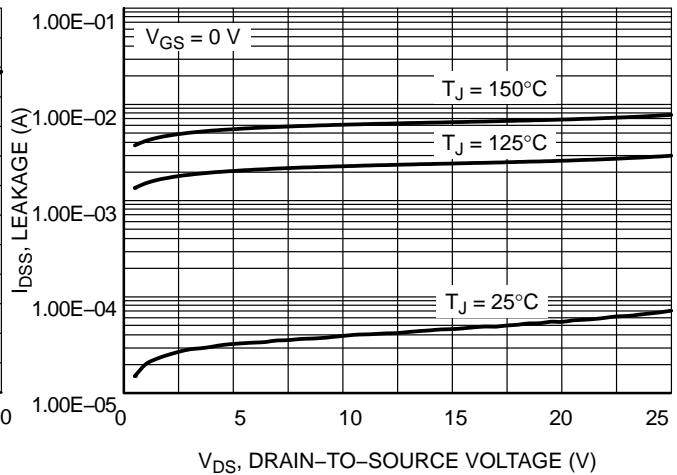


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

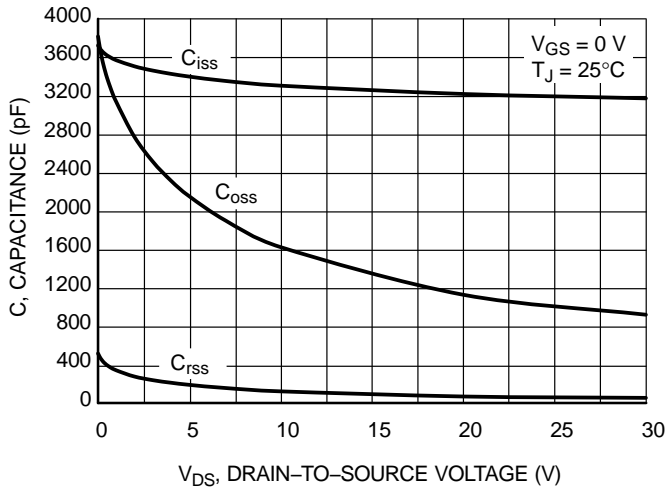


Figure 7. Capacitance Variation

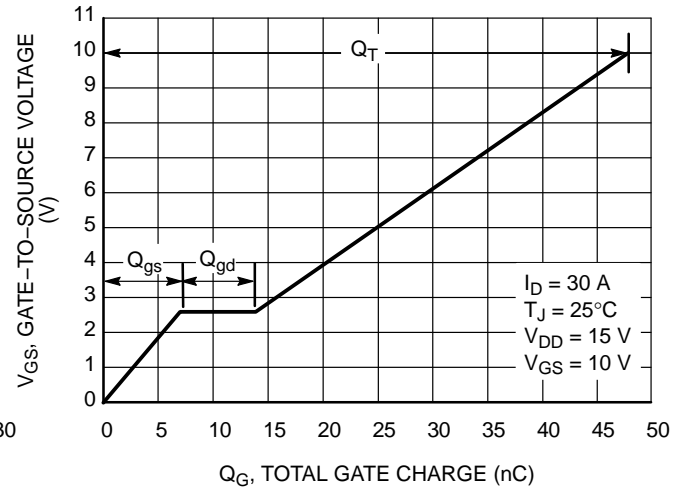


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

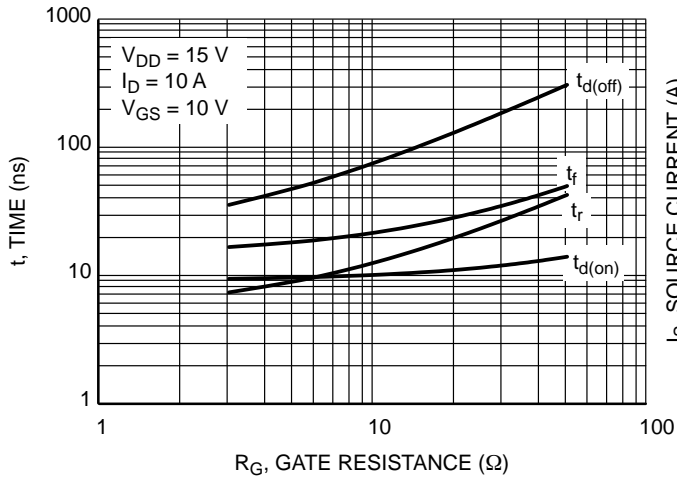


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

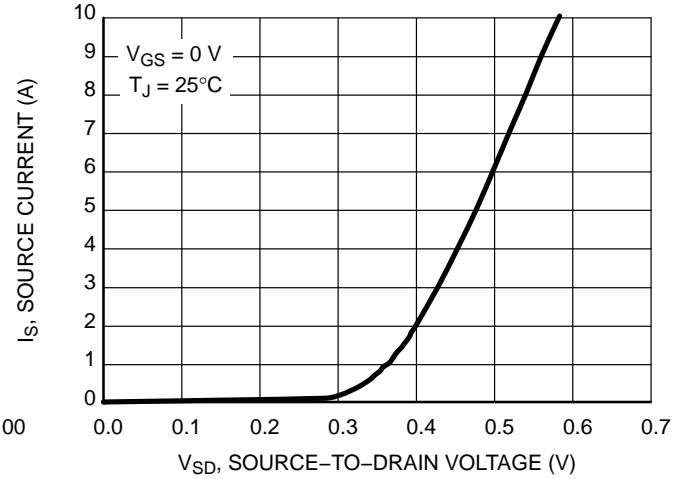


Figure 10. Diode Forward Voltage vs. Current

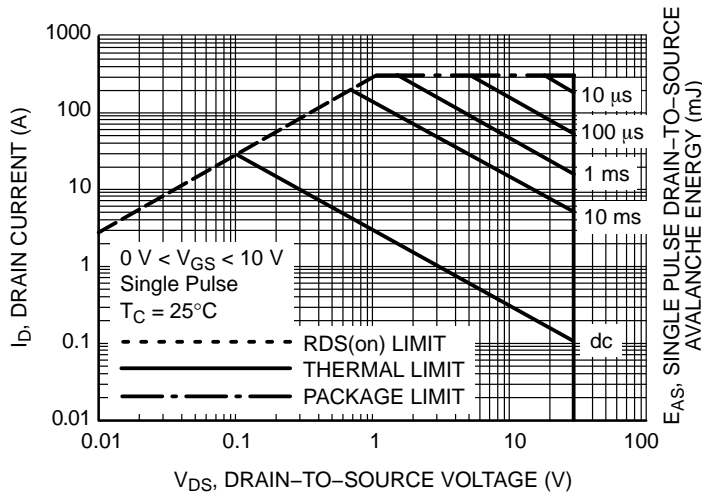


Figure 11. Maximum Rated Forward Biased Safe Operating Area

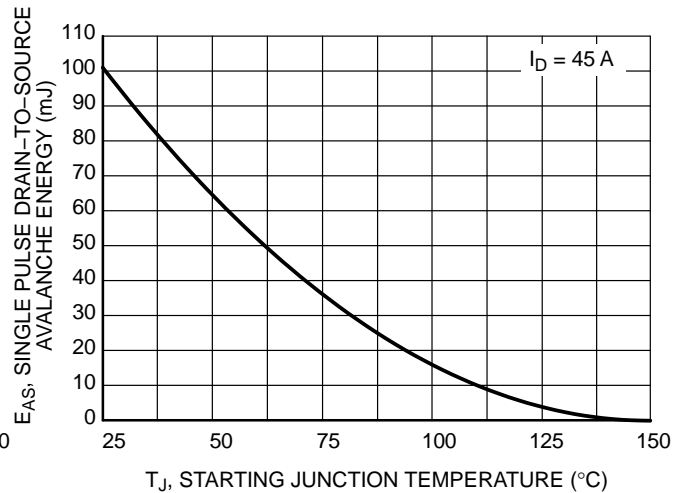


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL PERFORMANCE CURVES

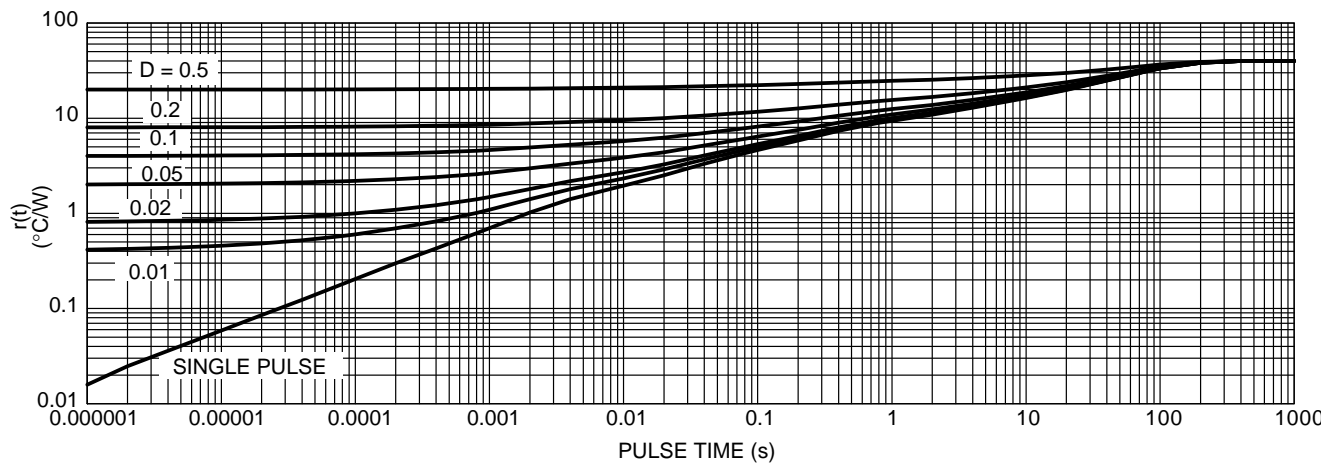


Figure 13. Thermal Response



SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

NOTES:

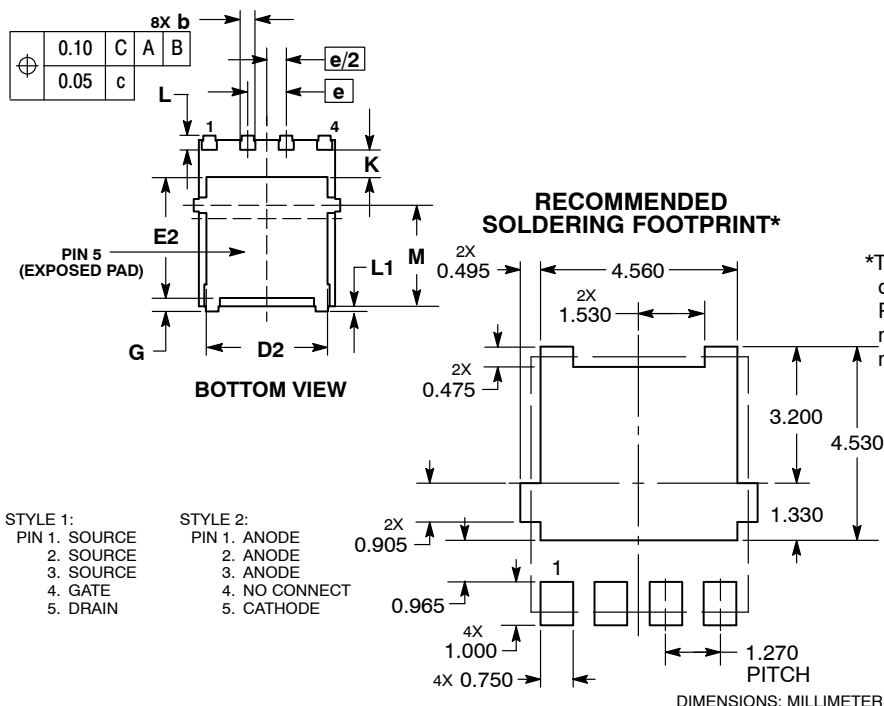
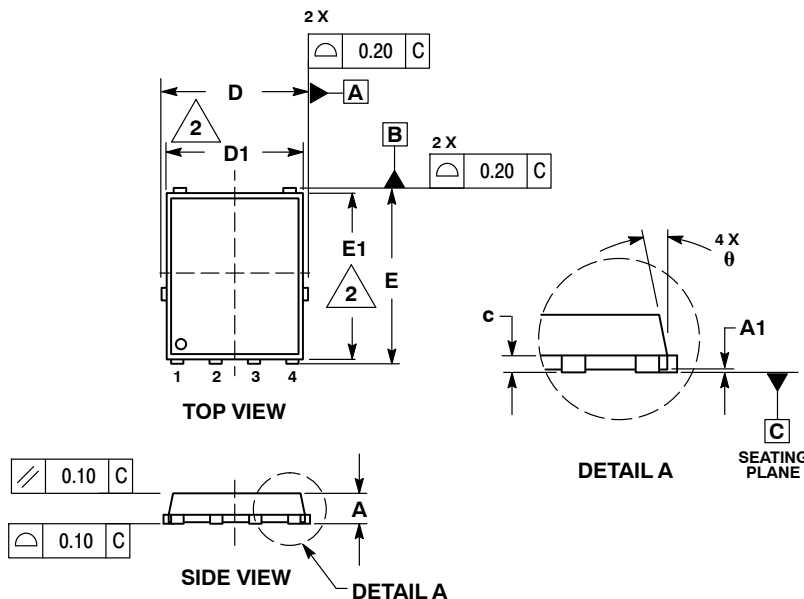
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC
MARKING DIAGRAM*


XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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